

Title (en)
NUCLEATION LAYER DEPOSITION METHOD

Title (de)
NUKLEATIONSSCHICHT-ABSCHIEDEVERFAHREN

Title (fr)
PROCÉDÉ DE SÉPARATION DE COUCHE DE NUCLÉATION

Publication
EP 3775334 A1 20210217 (DE)

Application
EP 19718284 A 20190410

Priority
• DE 102018108604 A 20180411
• EP 2019059010 W 20190410

Abstract (en)
[origin: WO2019197433A1] The invention relates to a method for depositing a nucleation layer (3) comprised of elements of the main groups III and V directly onto the surface (2) of a substrate (1) made of an element of the main group IV, wherein together with a first gaseous starting material containing the element of the main group III, a second gaseous starting material containing the element of the main group V is introduced at a process temperature of greater than 500°C into a process chamber (8) containing the substrate (1). It is essential that at least at the start of the deposition process, a third gaseous starting material containing an element of the main group IV is fed into the process chamber (8), together with the first and second gaseous starting material, which third gaseous starting material develops an n-doping effect in the deposited III-V crystal, wherein a damping decrease is achieved at a dopant concentration of $< 1 \times 10^{18} \text{cm}^{-3}$.

IPC 8 full level
C30B 25/16 (2006.01); **C23C 16/00** (2006.01); **C30B 25/18** (2006.01); **C30B 29/40** (2006.01); **H01L 21/00** (2006.01)

CPC (source: EP KR US)
C23C 16/0218 (2013.01 - EP KR US); **C23C 16/303** (2013.01 - EP KR US); **C30B 25/165** (2013.01 - EP KR US); **C30B 25/183** (2013.01 - EP KR US); **C30B 29/403** (2013.01 - EP KR US); **H01L 21/02381** (2013.01 - EP KR US); **H01L 21/02458** (2013.01 - EP KR US); **H01L 21/02502** (2013.01 - US); **H01L 21/0254** (2013.01 - EP KR US); **H01L 21/02576** (2013.01 - EP KR US); **H01L 21/0262** (2013.01 - EP KR US); **H01L 21/02661** (2013.01 - EP KR); **H01L 29/2003** (2013.01 - KR); **H01L 29/207** (2013.01 - US); **H01L 29/66462** (2013.01 - EP KR US); **H01L 29/7786** (2013.01 - KR US); **H01L 29/2003** (2013.01 - EP US); **H01L 29/205** (2013.01 - US); **H01L 29/7786** (2013.01 - EP)

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)
BA ME

DOCDB simple family (publication)
WO 2019197433 A1 20191017; CN 112135933 A 20201225; CN 112135933 B 20230203; DE 102018108604 A1 20191017; EP 3775334 A1 20210217; JP 2021520643 A 20210819; JP 7441794 B2 20240301; KR 102583794 B1 20230927; KR 20200141081 A 20201217; TW 201945573 A 20191201; US 11887848 B2 20240130; US 2022051893 A1 20220217

DOCDB simple family (application)
EP 2019059010 W 20190410; CN 201980032612 A 20190410; DE 102018108604 A 20180411; EP 19718284 A 20190410; JP 2020554883 A 20190410; KR 20207032374 A 20190410; TW 108112517 A 20190410; US 201917046714 A 20190410